

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _D MAX T _C = +25°C
60V	1.6mΩ @ V _{GS} = 10V	205A

Features

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Description and Applications

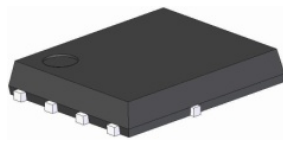
This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in power management and load switch.

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

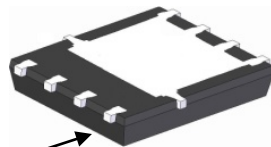
Mechanical Data

- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

PowerDI5060-8 (Type K)

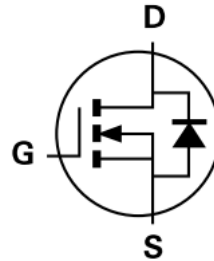


Top View

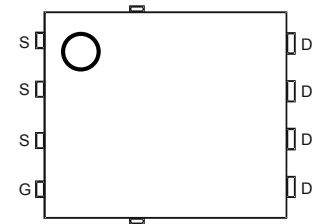


Pin1

Bottom View



Internal Schematic



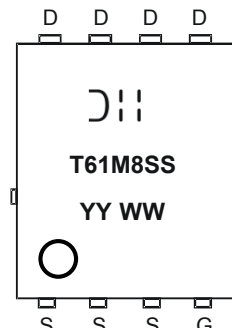
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT61M8SPS-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, “Green” and Lead-free.
 3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



- D;| = Manufacturer's Marking
T61M8SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 21 = 2021)
WW = Week (01 to 53)

Maximum Ratings (@ $T_C = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	I_D	$T_C = +25^\circ\text{C}$	205
		$T_C = +70^\circ\text{C}$	160
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	205	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	820	A
Pulsed Body Diode Forward Current (10 μs Pulse, Duty Cycle = 1%)	I_{SM}	820	A
Avalanche Current, $L = 1\text{mH}$	I_{AS}	35.8	A
Avalanche Energy, $L = 1\text{mH}$	E_{AS}	640.8	mJ

Thermal Characteristics (@ $T_C = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	P_D	139	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	0.9	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_C = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.1	1.6	m Ω	$V_{GS} = 10\text{V}, I_D = 30\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 20\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	8306	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	2735	—		
Reverse Transfer Capacitance	C_{rss}	—	184	—		
Gate Resistance	R_g	—	3.0	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge	Q_g	—	130.6	—	nC	$V_{DS} = 30\text{V}, I_D = 30\text{A}, V_{GS} = 10\text{V}$
Gate-Source Charge	Q_{gs}	—	30.4	—		
Gate-Drain Charge	Q_{gd}	—	28.1	—		
Turn-On Delay Time	$t_{D(ON)}$	—	11.3	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, I_D = 30\text{A}, R_g = 3\Omega$
Turn-On Rise Time	t_R	—	28.5	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	86.2	—		
Turn-Off Fall Time	t_F	—	47.6	—		
Body Diode Reverse Recovery Time	t_{RR}	—	70.4	—	ns	$I_F = 30\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	127	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

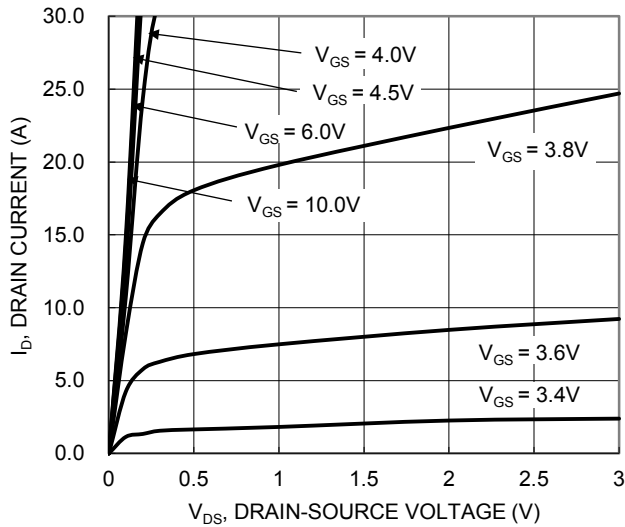


Figure 1. Typical Output Characteristic

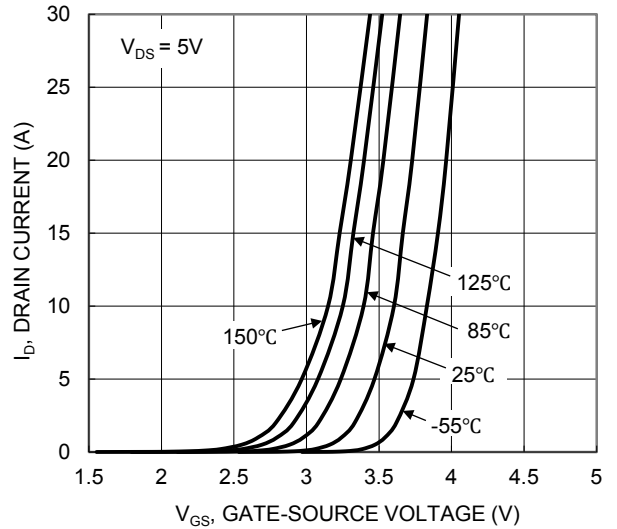


Figure 2. Typical Transfer Characteristic

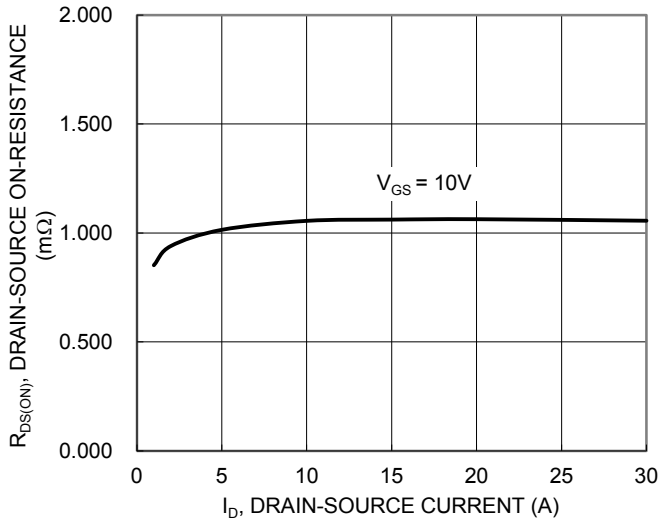


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

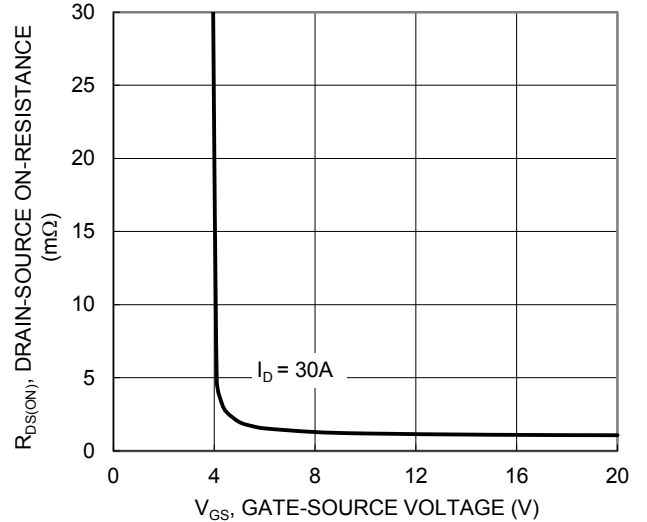


Figure 4. Typical Transfer Characteristic

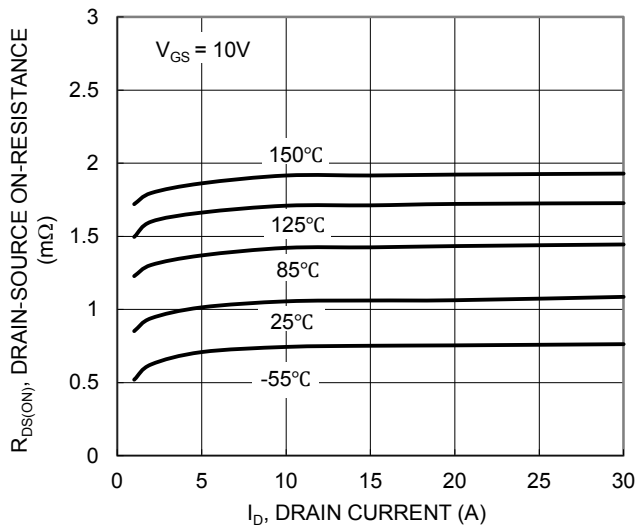


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

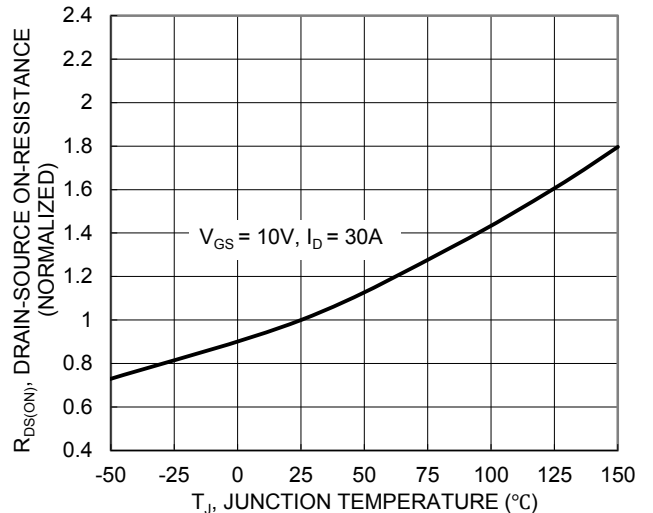


Figure 6. On-Resistance Variation with Temperature

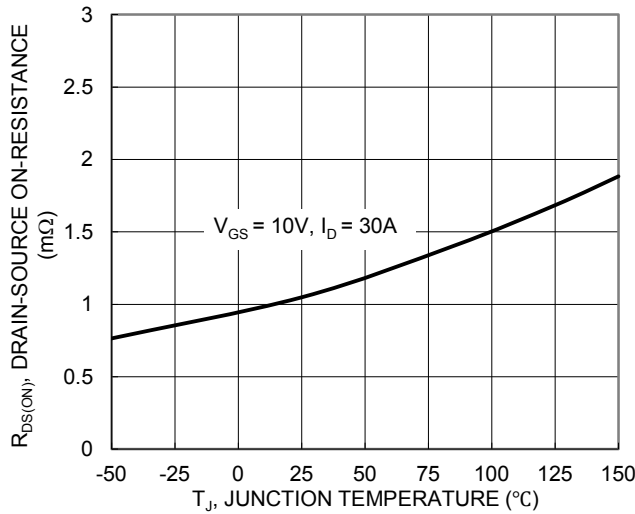


Figure 7. On-Resistance Variation with Temperature

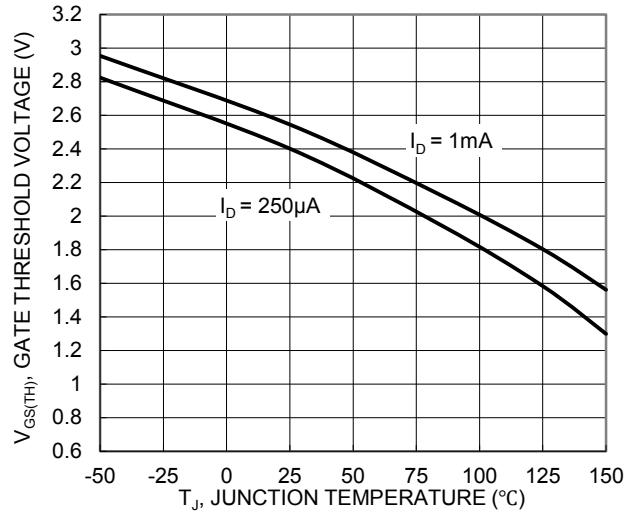


Figure 8. Gate Threshold Variation vs. Junction Temperature

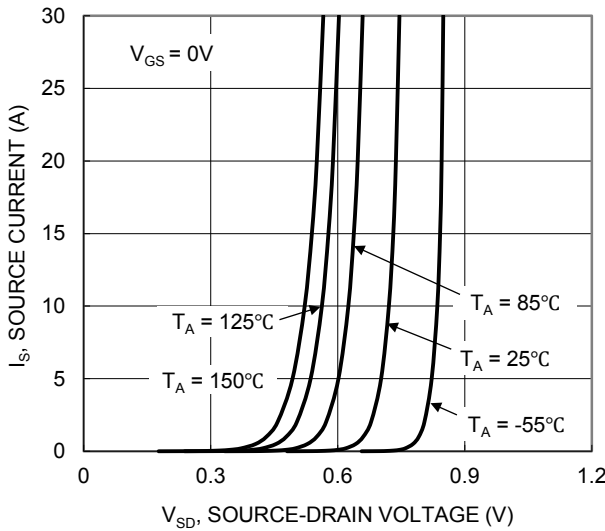


Figure 9. Diode Forward Voltage vs. Current

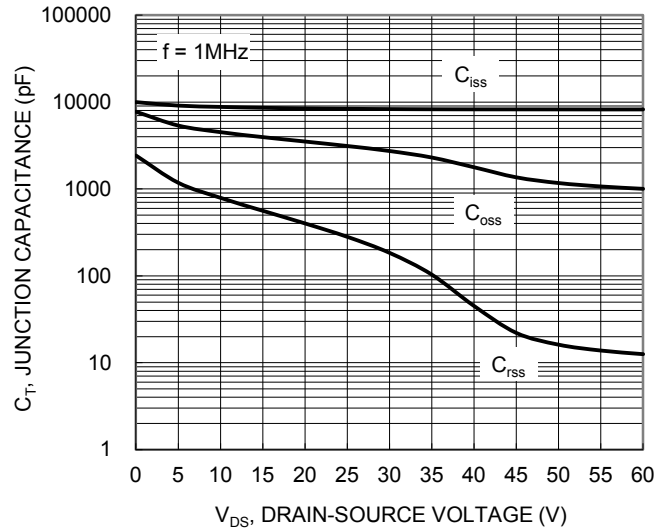


Figure 10. Typical Junction Capacitance

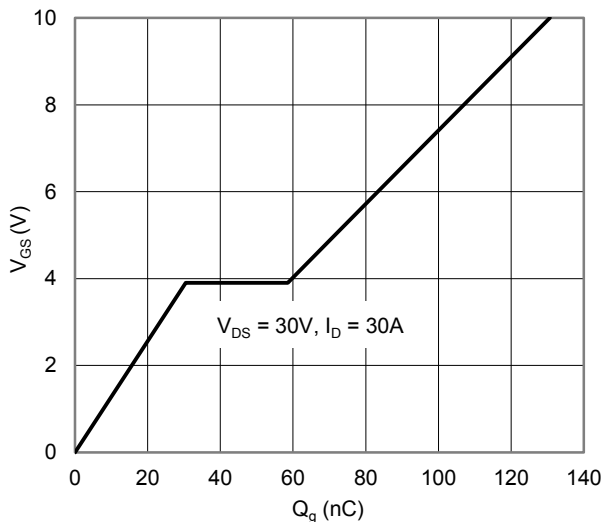


Figure 11. Gate Charge

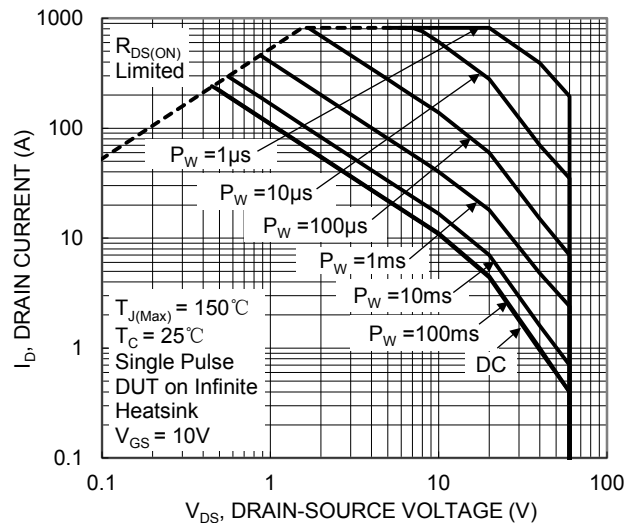


Figure 12. SOA, Safe Operation Area

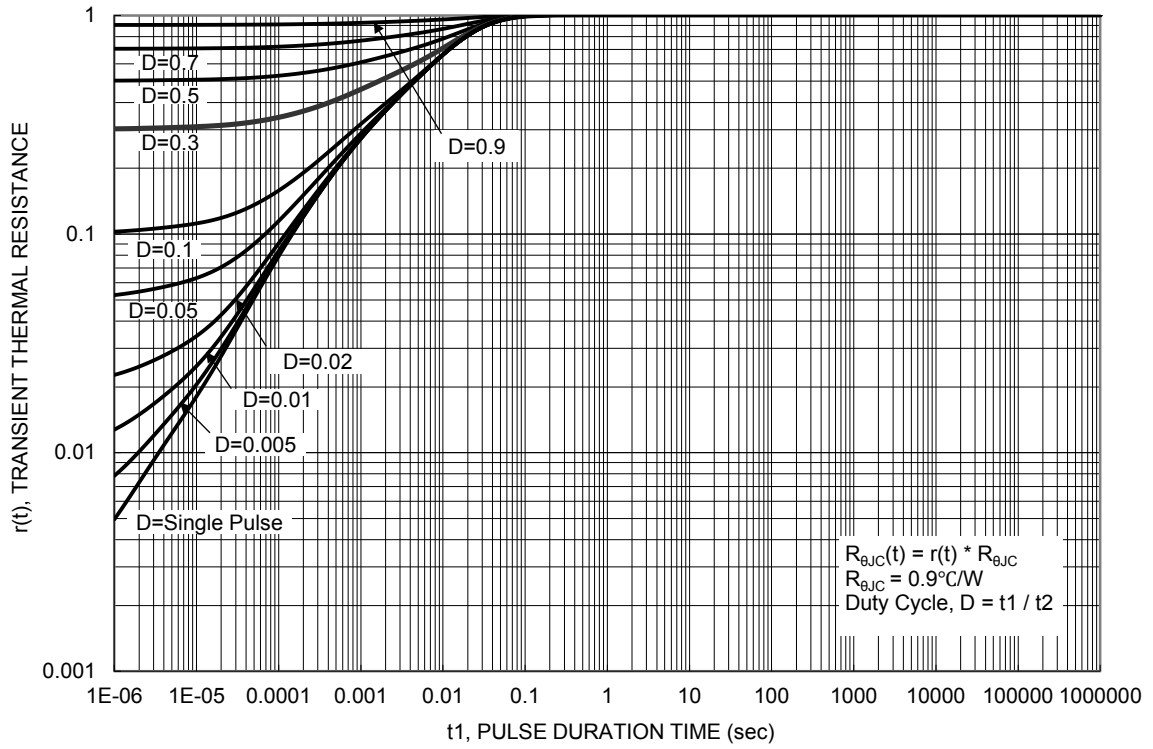
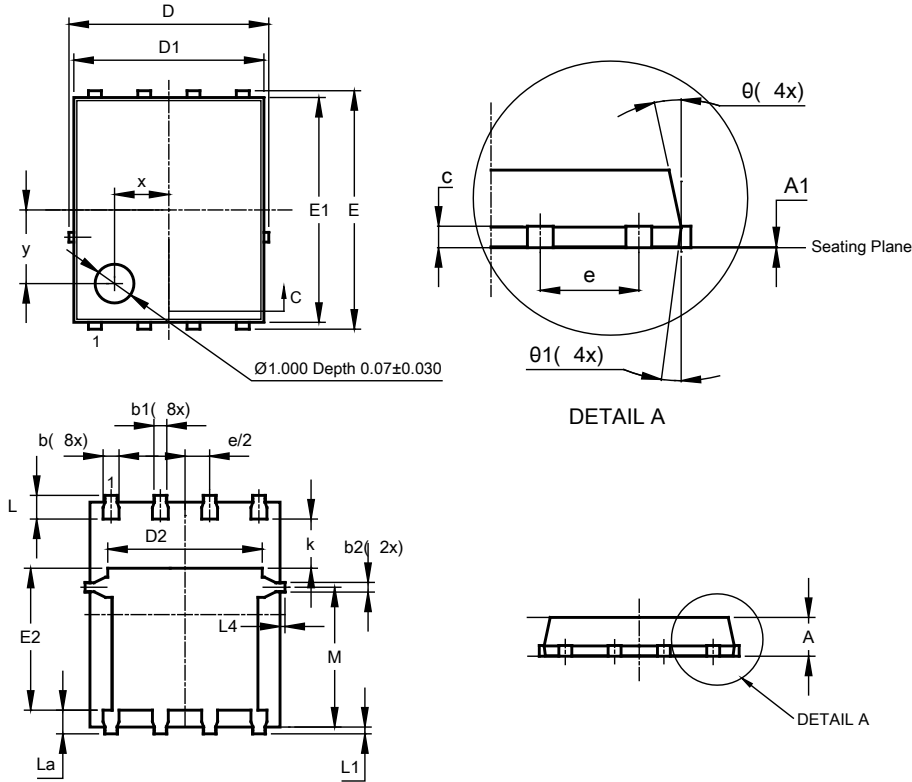


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)

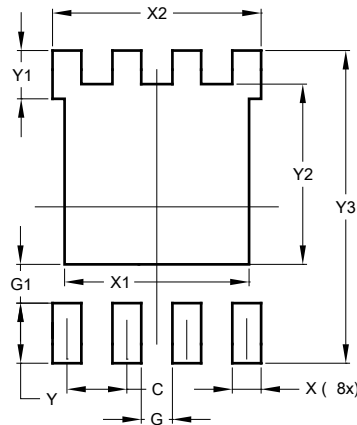


PowerDI5060-8 (Type K)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	0.02
b	0.33	0.51	0.41
b1	0.300	0.366	0.333
b2	0.20	0.35	0.25
c	0.23	0.33	0.277
D	5.15 BSC		
D1	4.85	4.95	4.90
D2	-	-	3.98
E	6.15 BSC		
E1	5.75	5.85	5.80
E2	3.56	3.725	3.66
e	1.27BSC		
k	-	-	1.27
L	0.51	0.71	0.61
La	0.51	0.675	0.61
L1	0.05	0.20	0.175
L4	-	-	0.125
M	3.50	3.71	3.605
x	-	-	1.400
y	-	-	1.900
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	3.910
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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